

Product Overview

NVH4L015N065SC1: Silicon Carbide MOSFET, N-Channel, 650V, 12 mΩ , TO247-4L

For complete documentation, see the data sheet.

Silicon Carbide (SiC) MOSFET uses a completely new technology that provide superior switching performance and higher reliability compared to Silicon. In addition, the low ON resistance and compact chip size ensure low capacitance and gate charge. Consequently, system benefits include highest efficiency, faster operation frequency, increased power density, reduced EMI, and reduced system size.

Features

- Qualified for Automotive According to AEC-Q101
- 650V rated
- Max RDS(on) = 18 mΩ at Vgs = 18V, Id = 75A
- High Speed Switching and Low Capacitance
- 100% UIL Tested
- Devices are RoHS Compliant

Benefits

- Automotive grade

Applications

- Automotive DC/DC and PFC
- Automotive Traction Inverter

End Products

- Automotive On Board Charger
- Automotive Traction Inverter

Part Electrical Specifications

Product	Pricing (\$/Unit)	Compliance	Status	Channel Polarity	Configuration	Blocking Voltage BV _{DSS} (V)	I _{D(max)} (A)	R _{DS(on)} Typ @ 25°C (mΩ)	Q _g Total (C)	Output Capacitance (C)	T _j Max (°C)	Package Type
NVH4L015N065SC1	15.9283	AEC Qualified PPAP Capable Pb-free Halide free	Active	N-Channel	Single	650	142	12	283	424	175	TO-247-4

For more information please contact your local sales support at www.onsemi.com.

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